

MR860 MR861 MR862 MR864 **MR866**

Data Sheet Designers

STUD MOUNTED **FAST RECOVERY POWER RECTIFIERS**

. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

FAST RECOVERY POWER RECTIFIERS

> 50-600 VOLTS **40 AMPERES**

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves - representing boundaries on device characteristics – are given to facilitate "worst case" design.



MAXIMUM RATINGS

Rating	Symbol	MR860	MR861	MR862	MR864	MR866	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	200	400	600	Volts
Non-Repetitive Peak Reverse Voltage	VRSM	75	150	250	450	650	Volts
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, TC = 100°C)	10	-		40			Amps
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	IFSM	-		— 350 —		-	Amps
Operating Junction Temperature Range	T	-		-65 to +16	60		°C
Storage Temperature Range	T _{stq}	-		-65 to +17	'5		°C

THERMAL CHARACTERISTICS

1	Characteristic	Symbol	Max	Unit
1	Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.85	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Instantaneous Forward Voltage (iF = 125 Amp, T _J = 150 ^o C)	٧F	-	1.3	1.6	Volts
Forward Voltage (iF = 40 Amp, T _C = 25°C)	VF	-	1.0	1.4	Volts
Reverse Current (rated dc voltage) $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$	IR	_ _	25 1.0	50 2.0	μA mA

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Recovery Time (I _F = 1.0 Amp to V _R = 30 Vdc, Figure 16) (I _{FM} = 36 Amp, di/dt = 25 A/µs, Figure 17)	^t rr	1 1	150 200	200 400	ns
Reverse Recovery Current (IF = 1.0 Amp to VR = 30 Vdc, Figure 16)	RM(REC)	-	2.0	3.0	Amp

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed

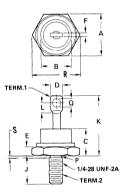
FINISH: All external surfaces corrosion

resistant and readily solderable

POLARITY: Cathode to Case

WEIGHT: 17 Grams (Approximately)

STUD TORQUE: 25 in. lbs.

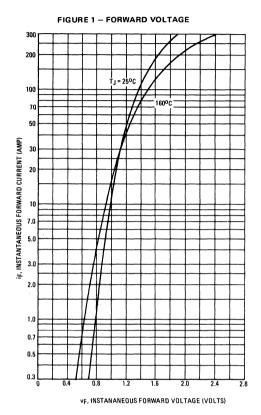


	MILLIMETERS			INCHES		
DIM	MIN	MAX	MIN	MAX		
Α	16.94	17.45	0.669	0.687		
В	~	16.94	_	0.667		
C	~	11.43	_	0.450		
D		9.53	_	0.375		
E	2.92	5.08	0,115	0.200		
F	~-	2.03	-	0.080		
J	10.72	11.51	0.422	0.453		
K		25.40	-	1.000		
L	3.86		0.156	-		
P	5.59	6.32	0.220	0.249		
Q	3.56	4.45	0.140	0.175		
R	-	20.16	_	0.794		
S	-	2.26	_	0.089		

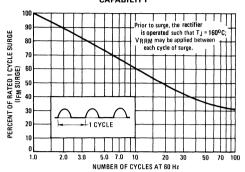
ANSI Y14.5, 1973.

- 1. DIM "P" IS DIA. 2. CHAMFER OR UNDERCUT ON ONE OR BOTH ENDS
 - OF HEXAGONAL BASE IS OPTIONAL.
- 3. ANGULAR ORIENTATION AND CONTOUR OF TERMINAL ONE IS OPTIONAL.
 4. THREADS ARE PLATED.
- 5. DIMENSIONING AND TOLERANCING PER

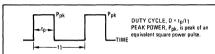
CASE 257-01 DO-5







NOTE 1



The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steedy-state conditions are achieved. Using the measured value of T.C., the junction temperature may be determined by:

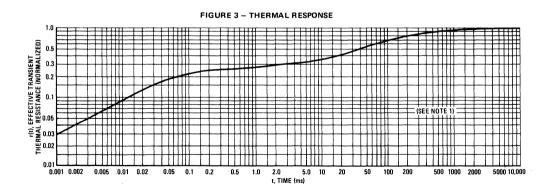
TJ = TC + 4 TJC

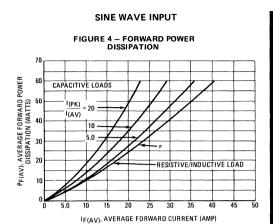
where $\triangle \, T_{JC}$ is the increase in junction temperature above the case temperature. It may be determined by:

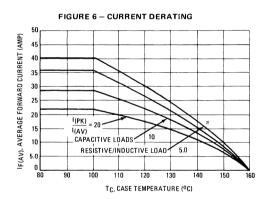
 $\Delta \, \mathsf{TJC} = \mathsf{P}_{\mathsf{DK}} \, \cdot \mathsf{R}_{\mathsf{\theta} \, \mathsf{JC}} \, [\, \mathsf{D} + (\mathsf{1} - \mathsf{D}) \, \cdot \mathsf{r}(\mathsf{t}_1 + \mathsf{t}_{\mathsf{p}}) + \mathsf{r}(\mathsf{t}_{\mathsf{p}}) - \mathsf{r}(\mathsf{t}_{\mathsf{1}}) \}$

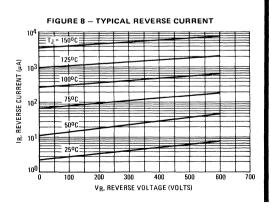
r(t) = normalized value of transient thermal resistance at time, t, from Figure

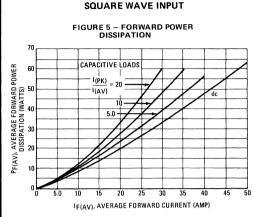
 $r(t_1 + t_p) = normalized value of transient thermal resistance at time <math>t_1 + t_p$.

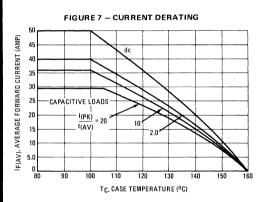


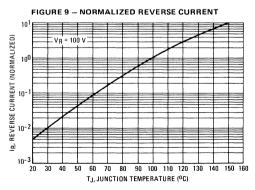


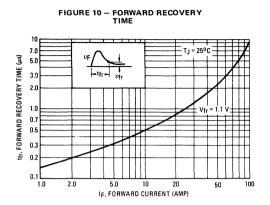


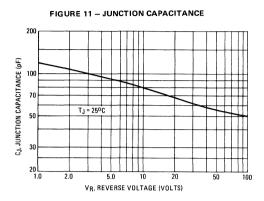




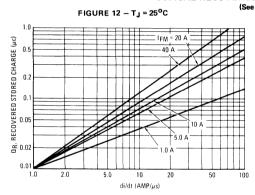


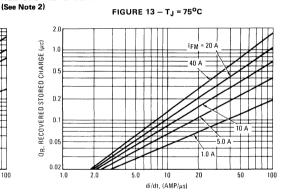


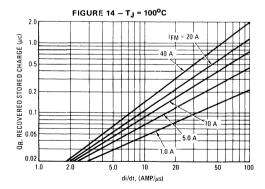




TYPICAL RECOVERED STORED CHARGE DATA







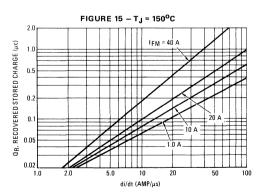
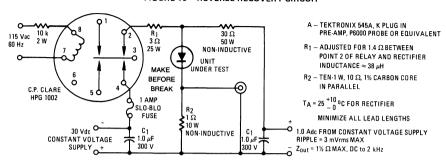
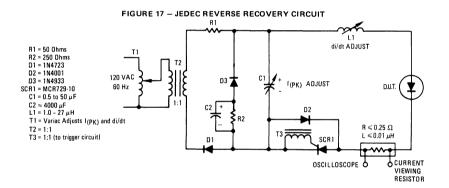


FIGURE 16 - REVERSE RECOVERY CIRCUIT





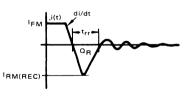
NOTE 2

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using $I_F=1.0\ A,\ V_R=30\ V.$ In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of $25^{0}C,\ 75^{0}C,\ 100^{0}C,\ and <math display="inline">150^{0}C.$

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation didt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current (I_{RM(REC)}) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt} \right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$